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CSD19503KCS

SLPS479A - DECEMBER 2013 - REVISED AUGUST 2014

CSD19503KCS 80-V N-Channel NexFET™ Power MOSFET

Features 1

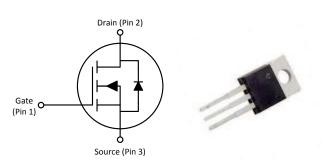
- Ultra-Low Q_a and Q_{ad}
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- **RoHS** Compliant
- Halogen Free
- **TO-220 Plastic Package**

2 Applications

- Secondary Side Synchronous Rectifier
- Motor Control

Description 3

This 80 V, 7.6 mΩ, TO-220 NexFET™ power MOSFET is designed to minimize losses in power conversion applications.



Product Summary

T _A = 25°	C	TYPICAL VA	UNIT	
V _{DS}	Drain-to-Source Voltage	80		V
Qg	Gate Charge Total (10 V)	28		nC
Q _{gd}	Gate Charge Gate-to-Drain	5.4	nC	
Р	Drain-to-Source On-Resistance	$V_{GS} = 6 V$	8.8	mΩ
R _{DS(on)}	Drain-to-Source On-Resistance	V _{GS} = 10 V	7.6	mΩ
V _{GS(th)}	Threshold Voltage	2.8		V

Ordering Information⁽¹⁾

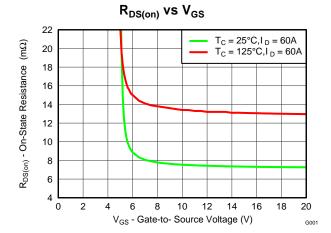
Device	Package	Media	Qty	Ship
CSD19503KCS	TO-220 Plastic Package	Tube	50	Tube

(1) For all available packages, see the orderable addendum at the end of the data sheet.

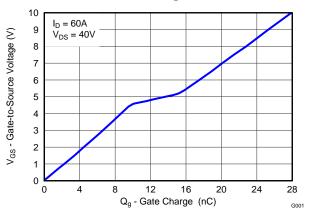
Absolute Maximum Ratings

T _A = 2	5°C	VALUE	UNIT					
V_{DS}	Drain-to-Source Voltage	80	V					
V_{GS}	Gate-to-Source Voltage	±20	V					
	Continuous Drain Current (Package limited)	100						
ID	Continuous Drain Current (Silicon limited), $T_C = 25^{\circ}C$	94	А					
	Continuous Drain Current (Silicon limited), $T_{C} = 100^{\circ}C$	66						
I _{DM}	Pulsed Drain Current ⁽¹⁾	247	А					
PD	Power Dissipation	188	W					
T _J , T _{stg}	Operating Junction and Storage Temperature Range	-55 to 175	°C					
E _{AS}	Avalanche Energy, single pulse I_D = 53 A, L = 0.1 mH, R_G = 25 Ω	140	mJ					

(1) Max $R_{\theta JC} = 0.8^{\circ}C/W$, pulse duration $\leq 100 \ \mu s$, Duty cycle $\leq 1\%$



Gate Charge



An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.



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4 Revision History

CI	hanges from Original (December 2013) to Revision A	age
•	Pulsed drain current increased from 113 to 247 A	1
•	Updated pulsed current conditions	1
•	Updated Figure 10 to reflect increased pulsed drain current	6

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5 Specifications

5.1 Electrical Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
STATIC	CHARACTERISTICS				
BV _{DSS}	Drain-to-Source Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$	80		V
I _{DSS}	Drain-to-Source Leakage Current	$V_{GS} = 0 V, V_{DS} = 64 V$		1	μA
I _{GSS}	Gate-to-Source Leakage Current	$V_{DS} = 0 V, V_{GS} = 20 V$		100	nA
V _{GS(th)}	Gate-to-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2.2 2.8	3.4	V
Р	Drain-to-Source On-Resistance	$V_{GS} = 6 V, I_{D} = 60 A$	8.8	10.9	mΩ
R _{DS(on)}	Drain-to-Source On-Resistance	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 60 \text{ A}$	7.6	9.2	mΩ
g _{fs}	Transconductance	V _{DS} = 8 V, I _D = 60 A	110		S
DYNAMI	C CHARACTERISTICS				
C _{iss}	Input Capacitance		2100	2730	pF
C _{oss}	Output Capacitance	$V_{GS} = 0 V, V_{DS} = 40 V, f = 1 MHz$	555	721	pF
C _{rss}	Reverse Transfer Capacitance		8.5	11.1	pF
R_{G}	Series Gate Resistance		1.2	2.4	Ω
Qg	Gate Charge Total (10 V)		28	36	nC
Q _{gd}	Gate Charge Gate-to-Drain		5.4		nC
Q _{gs}	Gate Charge Gate-to-Source	$V_{\rm DS} = 40$ V, I _D = 60 A	9.8		nC
Q _{g(th)}	Gate Charge at V _{th}		6.1		nC
Q _{oss}	Output Charge	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$	71		nC
t _{d(on)}	Turn On Delay Time		7		ns
t _r	Rise Time	V _{DS} = 40 V, V _{GS} = 10 V,	3		ns
t _{d(off)}	Turn Off Delay Time	$I_{DS} = 60 \text{ A}, \text{ R}_{G} = 0 \Omega$	11		ns
t _f	Fall Time		2		ns
DIODE C	HARACTERISTICS	•			
V_{SD}	Diode Forward Voltage	I _{SD} = 60 A, V _{GS} = 0 V	0.9	1.1	V
Q _{rr}	Reverse Recovery Charge	V_{DS} = 40 V, I _F = 60 A,	119		nC
t _{rr}	Reverse Recovery Time	di/dt = 300 A/µs	72		ns

5.2 Thermal Information

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	THERMAL METRIC	MIN	TYP	MAX	UNIT
$R_{ extsf{ heta}JC}$	Junction-to-Case Thermal Resistance			0.8	°C/W
$R_{\theta J A}$	Junction-to-Ambient Thermal Resistance			62	°C/W

CSD19503KCS

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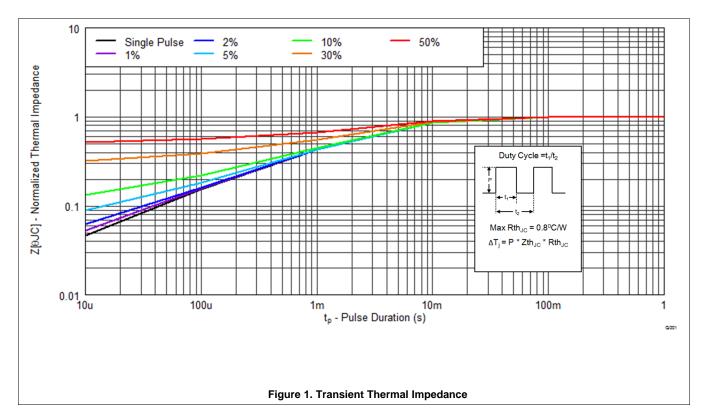
INSTRUMENTS

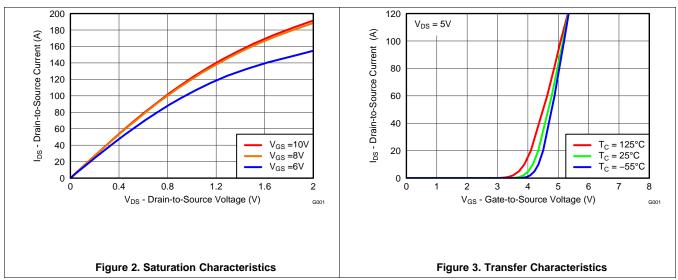
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5.3 Typical MOSFET Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

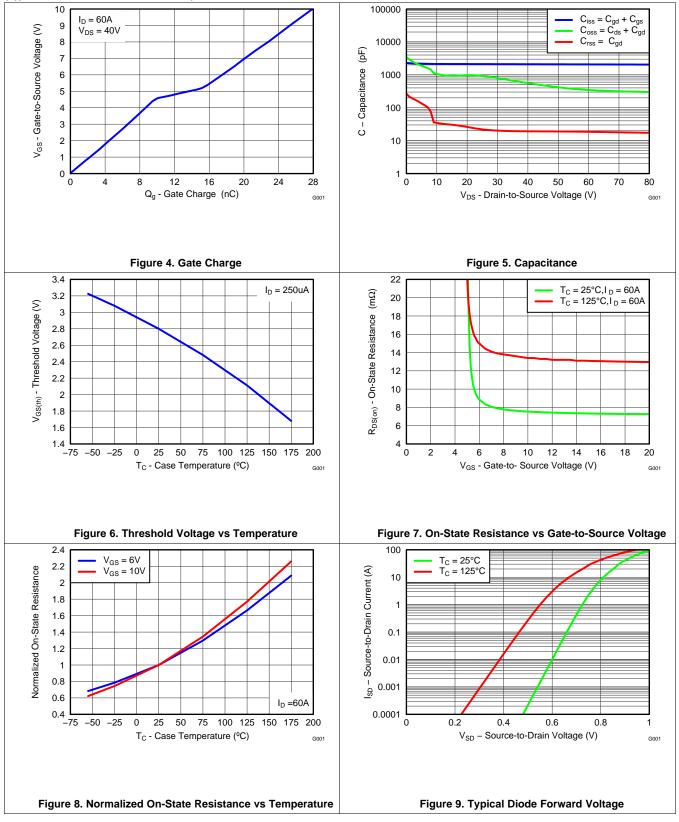






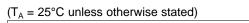
Typical MOSFET Characteristics (continued)

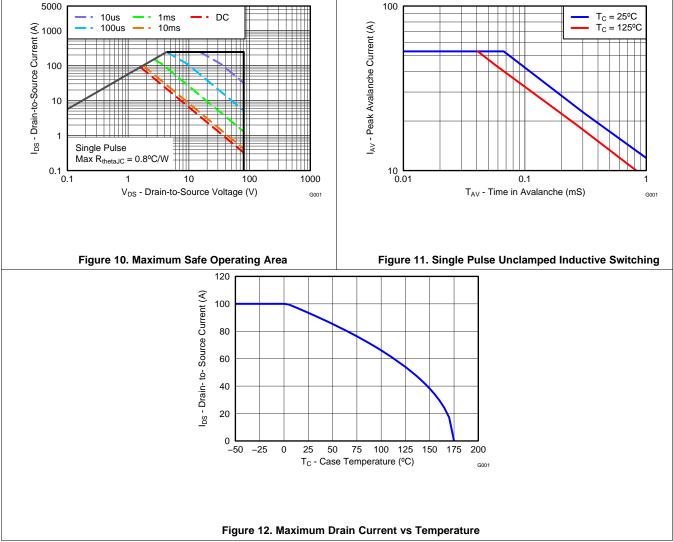
 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$





Typical MOSFET Characteristics (continued)







6 Device and Documentation Support

6.1 Trademarks

NexFET is a trademark of Texas Instruments.

6.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

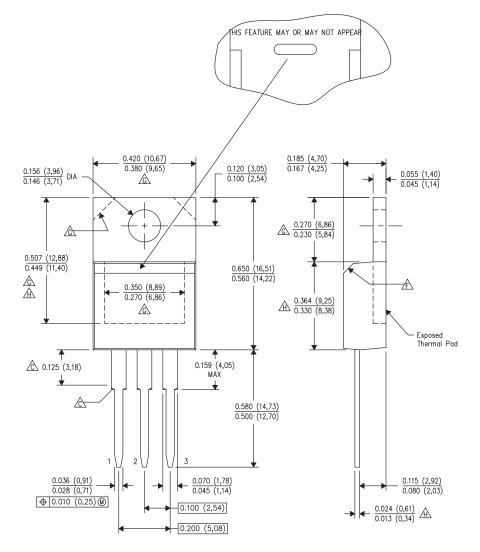
TEXAS INSTRUMENTS

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7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 KCS Package Dimensions



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Lead dimensions are not controlled within this area. Chamfer may or may not appear
- D. All lead dimensions apply before solder dip.
 E. The center lead is in electrical contact with the mounting tab.
- \triangle The chamfer is optional.
- Thermal pad contour optional within these dimensions.
- <u>CC</u> Inermal pad contour optional within these dimensions.
 <u>A</u> Falls within JEDEC TO-220 variation AB, except minimum lead thickness, minimum exposed pad length,
 - H Falls within JEDEC T0-220 variation and maximum body length.

Pin Configuration

J									
Position	Designation								
Pin 1	Gate								
Pin 2 / Tab	Drain								
Pin 3	Source								



30-Apr-2016

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD19503KCS	ACTIVE	TO-220	KCS	3	50	Pb-Free (RoHS)	CU SN	N / A for Pkg Type	-55 to 150	CSD19503KCS	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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